

N-channel TrenchMOS standard level FET Rev. 02 — 16 December 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

DC-to-DC converters

General purpose switching

1.4 Quick reference data

Quick reference data					
Parameter	Conditions	Min	Тур	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	200	V
drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}$	-	-	20	А
total power dissipation	T _{mb} = 25 °C	-	-	150	W
aracteristics					
drain-source on-state resistance	V_{GS} = 10 V; I _D = 10 A; T _j = 25 °C	-	120	130	mΩ
characteristics					
gate-drain charge	V _{GS} = 10 V; I _D = 20 A; V _{DS} = 160 V; T _j = 25 °C	-	22	-	nC
	Parameter drain-source voltage drain current total power dissipation tracteristics drain-source on-state resistance characteristics	ParameterConditionsdrain-source voltage $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$ drain current $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}$ total power dissipation $T_{mb} = 25 \text{ °C}$ total power dissipation $T_{mb} = 25 \text{ °C}$ tracteristics $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ resistance $T_j = 25 \text{ °C}$ characteristics $V_{GS} = 10 \text{ V}; I_D = 20 \text{ A};$	ParameterConditionsMindrain-source voltage $T_j \ge 25 \ ^\circ C; \ T_j \le 175 \ ^\circ C$ -drain current $T_{mb} = 25 \ ^\circ C; \ V_{GS} = 10 \ V$ -total power dissipation $T_{mb} = 25 \ ^\circ C$ -tracteristics $T_{mb} = 25 \ ^\circ C$ -drain-source on-state resistance $V_{GS} = 10 \ V; \ I_D = 10 \ A;$ $T_j = 25 \ ^\circ C$ -characteristics $V_{GS} = 10 \ V; \ I_D = 20 \ A;$ -gate-drain charge $V_{GS} = 10 \ V; \ I_D = 20 \ A;$ -	ParameterConditionsMinTypdrain-source voltage $T_j \ge 25 \ ^\circC; T_j \le 175 \ ^\circC$ drain current $T_{mb} = 25 \ ^\circC; V_{GS} = 10 \ ^\circC$ total power dissipation $T_{mb} = 25 \ ^\circC$ total power dissipation $T_{mb} = 25 \ ^\circC$ tracteristics $T_{mb} = 25 \ ^\circC$ drain-source on-state resistance $V_{GS} = 10 \ V; \ I_D = 10 \ A;$ $T_j = 25 \ ^\circC$ -120characteristics $V_{GS} = 10 \ V; \ I_D = 20 \ A;$ -22	ParameterConditionsMinTypMaxdrain-source voltage $T_j \ge 25 \ ^{\circ}C; \ T_j \le 175 \ ^{\circ}C$ 200drain current $T_{mb} = 25 \ ^{\circ}C; \ V_{GS} = 10 \ V$ 20total power dissipation $T_{mb} = 25 \ ^{\circ}C$ 150tracteristicstotal source on-state $V_{GS} = 10 \ V; \ I_D = 10 \ A;$ -120130characteristicstotal source on-state $V_{GS} = 10 \ V; \ I_D = 20 \ A;$ -22-

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHB20NQ20T	D2PAK	plastic gle-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

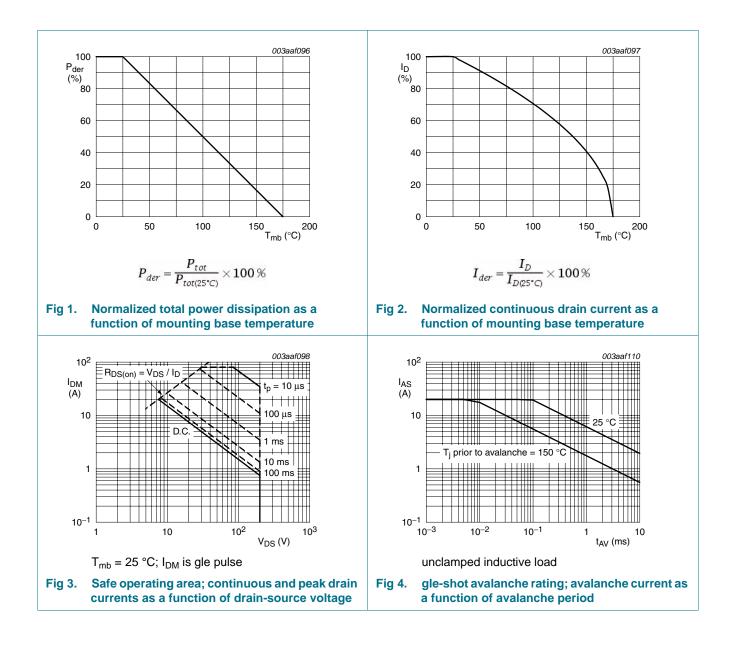
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	200	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	200	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C	-	14	А
		V _{GS} = 10 V; T _{mb} = 25 °C	-	20	А
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C	-	80	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	150	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	20	А
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	80	А
Avalanche r	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_{\text{D}} = 19 \text{ A}; \\ V_{sup} \leq 25 \text{ V}; \text{ unclamped}; \text{t}_{p} = 100 \mu\text{s}; \\ R_{GS} = 50 \Omega $	-	252	mJ
I _{AS}	non-repetitive avalanche current	$ \begin{aligned} V_{sup} &\leq 25 \text{ V}; V_{GS} = 10 \text{V}; \text{T}_{j(init)} = 25 ^\circ\text{C}; \\ \text{R}_{GS} &= 50 \Omega; \text{ unclamped} \end{aligned} $	-	20	А
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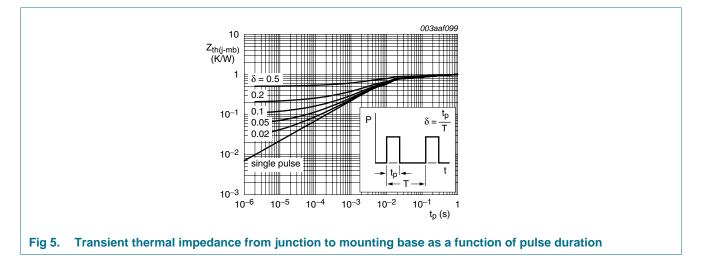
Table C

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5. Thermal characteristics

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Table 5.	I nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board ; minimum footprint	-	50	-	K/W



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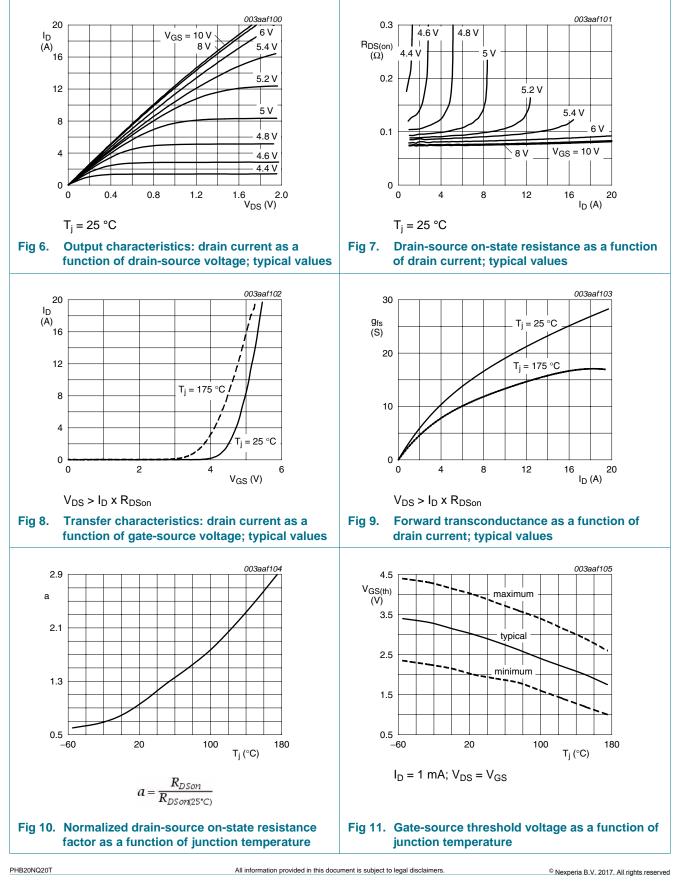
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _{(BR)DSS}	V _{(BR)DSS} drain-source breakdown	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	178	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	200	-	-	V
V _{GS(th)}	V _{GS(th)} gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
I _{DSS}	drain leakage current	V_{DS} = 200 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μΑ
		V_{DS} = 200 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μΑ
I _{GSS} gate leakage current	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	0.02	100	nA
	V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	0.02	100	nA	
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 10 A; T _j = 175 °C	-	-	377	mΩ
	resistance	V_{GS} = 10 V; I _D = 10 A; T _j = 25 °C	-	120	130	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 160 \text{ V}; V_{GS} = 10 \text{ V};$	-	65	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \ ^{\circ}C$	-	10	-	nC
Q _{GD}	gate-drain charge		-	22	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$	-	2470	-	pF
C _{oss}	output capacitance	$T_j = 25 \ ^{\circ}C$	-	207	-	pF
C _{rss}	reverse transfer capacitance		-	90	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 100 V; R_L = 4.7 Ω ; V_{GS} = 10 V;	-	15	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \ \Omega; T_j = 25 \ ^{\circ}C$	-	46	-	ns
t _{d(off)}	turn-off delay time		-	50	-	ns
t _f	fall time		-	38	-	ns
L _D	internal drain inductance	measured from tab to centre of die ; T_{j} = 25 $^{\circ}\text{C}$	-	3.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_{S} = 20 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	0.95	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/µs;	-	124	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 25 V; T_j = 25 °C	-	0.74	-	μC

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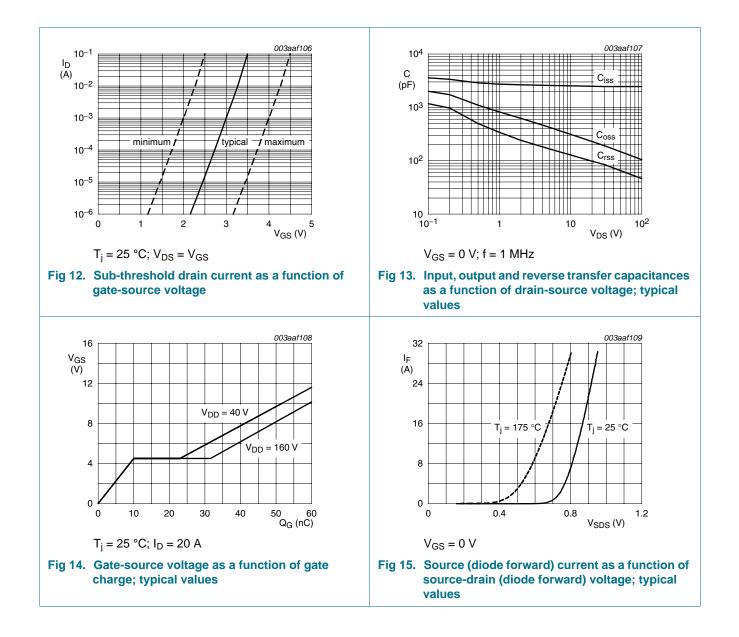
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7. Package outline

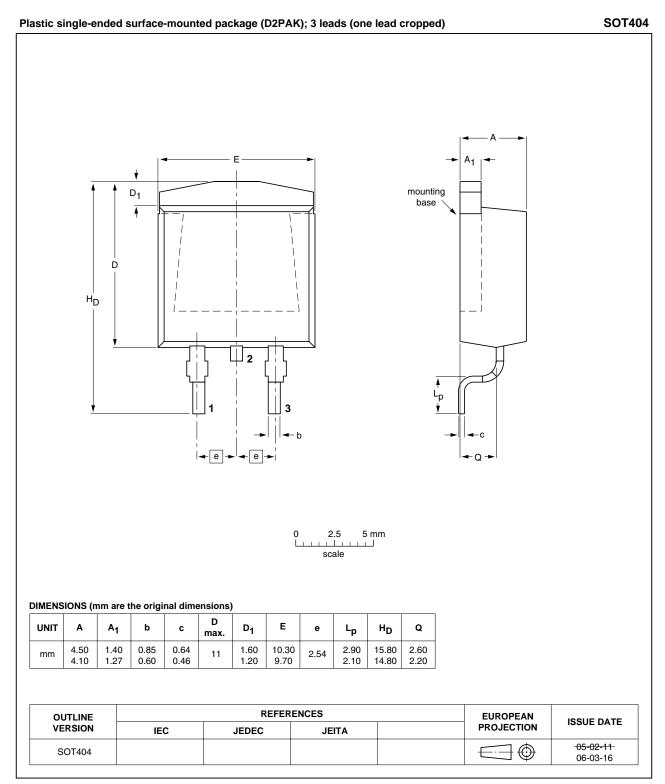


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PHB20NQ20T v.2	20101216	Product data sheet	-	PHB_PHP20NQ20T v.1
Modifications:	guidelines of • Legal texts	of NXP Semiconductors have been adapted to the	ne new company name	nply with the new identity e where appropriate. PHB_PHP20NQ20T v.1.
PHB_PHP20NQ20T v.1	19990801	Product specification	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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